Accepted Manuscript

Title: Morphological features of silicon substrate by using different frequency laser ablation in air andwater

Author: J.Y. Xu H. Hu Y.L. Lei



PII:	S0169-4332(14)01772-3
DOI:	http://dx.doi.org/doi:10.1016/j.apsusc.2014.08.038
Reference:	APSUSC 28491
To appear in:	APSUSC
Received date:	4-6-2014
Revised date:	9-7-2014
Accepted date:	7-8-2014

Please cite this article as: J.Y. Xu, H. Hu, Y.L. Lei, Morphological features of silicon substrate by using different frequency laser ablation in air andwater, *Applied Surface Science* (2014), http://dx.doi.org/10.1016/j.apsusc.2014.08.038

This is a PDF file of an unedited manuscript that has been accepted for publication. As a service to our customers we are providing this early version of the manuscript. The manuscript will undergo copyediting, typesetting, and review of the resulting proof before it is published in its final form. Please note that during the production process errors may be discovered which could affect the content, and all legal disclaimers that apply to the journal pertain.

ACCEPTED MANUSCRIPT

The author affiliation, abstract and figure captions are listed as follows:

Author Affiliation: J. Y. Xu, H. Hu^{*}, Y. L. Lei. Shenzhen Engineering Lab of Industrial Robots and Systems, Harbin Institute of Technology Shenzhen Graduate School, Shenzhen, Guangdong, 518055 China

Abstract: The interaction of the nanosecond laser (FWHM=30ns, ?=355nm) and monocrystalline silicon is investigated in air and water. Conventional optical and scanning electron microscopes are used to characterize surface ablation of the monocrystalline silicon. A numerical model is used to ascertain the time of the bubble motion in water. Morphological features of the laser-induced crater are different under various environments and frequencies. More debris is found when using high frequency ablation, and a larger zone is affected by heat when using low frequency ablation in air. There is no debris found in water, and the morphology of craters is better in low frequency ablation than that in high frequency ablation because bubbles generated by high frequency ablation affect laser transmission.

Figure Caption:

Fig. 1 Schematic of wafer singulation configuration Fig. 2 SEM images of silicon after nanosecond laser ablation in air (a) 3Hz

(b) 2 kHz (c) 100 kHz (d) Low magnification images of 100 pulses Fig. 3 Schematic of the laser ablation mechanism in air [28] Fig. 4. SEM images of silicon after nanosecond laser ablation in water (a) 3Hz (b) 2kHz (c) 100kHz Fig. 5. Schematic of the influence of bubbles in laser spread Fig. 6. The relationship between velocities versus time

Certification of the second se

Download English Version:

https://daneshyari.com/en/article/5361036

Download Persian Version:

https://daneshyari.com/article/5361036

Daneshyari.com